ABSTRACT OF THE DISCLOSURE

A semiconductor laser, including: an n-type cladding layer that has n-type conductivity; an active layer formed on top of the n-type cladding layer; a p-type cladding base layer that is formed on top of the active layer and has p-type conductivity;a current-blocking layer that is formed on specified parts of an upper surface of the p-type cladding base layer and substantially has n-type conductivity; and a p-type buried cladding layer that has p-type conductivity and is formed so as to cover the current-blocking layer and contact remaining parts of the upper surface of the p-type cladding base layer. The current-blocking layer has at least two regions having different concentrations (hereafter "N1" and "N2" where N1<N2) of n-type carriers, a region adjacent to an interface between the p-type cladding base layer and the p-type buried cladding layer having the N1 concentration of n-type carriers and a part or all of a remaining region of the current-blocking layer region having the N2 concentration.